IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:		PATENT APPLICATION
Inventors:	Yoshi Ono, John F. Conley, Jr., and Pooran Chandra Joshi	
Serial No:	Not Yet Assigned	Attorney Docket No. SLA0830
Filed:	Herewith	
Title:	CHARGE TRAP NON-VOLATILE MEMORY STRUCTURE FOR 2 BITS PER TRANSISTOR	

DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that my residence, post office address and citizenship are as stated below next to my name; I believe that I am the original, first and sole inventor (if one name is listed below), or the first and joint inventor (if plural names are listed below), of the subject matter which is claimed and for which a patent is sought on the invention entitled,

CHARGE TRAP NON-VOLATILE MEMORY STRUCTURE FOR 2 BITS PER TRANSISTOR

the specification of which (check applicable ones):

X is attached hereto;

_ was filed with the above-identified "Filed" date and assigned the above-identified "Serial No.";

_ was amended on (or amended through) _____.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment(s) referred to above.

I acknowledge the duty to disclose information, which is material to the examination of the application in accordance with Title 37, Code of Federal Regulations, §1.56.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Full name of sole or first inventor: Yoshi Ono

Residence: 2526 NW 24th Circle
Camas, WA98607

Post Office Address: Same

Citizenship: USA

Inventor's signature: _____

Date: 3/19/2004

****

Full name of second inventor: John F. Conley, Jr.

Residence: 4652 NW Walden St.
Camas, WA 98607

Post Office Address: Same

Citizenship: U.S.A.

Inventor's signature: _____

Date: 3/19/04

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Full name of third inventor: Pooran Chandra Joshi

Residence: 3205 NE 180th Court
Vancouver, WA 98682

Citizenship: India

Inventor's signature: _____

Date: 03/19/04

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POWER OF ATTORNEY BY ASSIGNEE

Sharp Laboratories of America, Inc., a corporation of the State of Washington, Assignee of the entire right, title and interest in and to the above-identified patent application by an assignment document filed herewith, hereby appoints David C. Ripma, Reg. No. 27,672, Matthew D. Rabdau, Reg. No. 43,026, as its attorneys with full power of substitution and revocation, to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith; said appointment to be to the exclusion of the inventor and the inventor's attorneys in accordance with the provisions of 37 C.F.R. §3.71.

Pursuant to 37 C.F.R. §3.73(b) the undersigned submits herewith the original of an assignment document from the inventor or inventors to Assignee, together with a cover sheet and the fee for recording same. The undersigned, whose title is supplied below, is authorized to sign this Power of Attorney on behalf of the Assignee.

Please direct all correspondence connected with this application to:

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Assignee:

Sharp Laboratories of America, Inc.

By: David C. Ripma
Title: Patent Counsel

Date: March 19, 2004